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Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	10	mA
				15	
I_H	I_T =100mA		MAX.	10	mA
dV/dt	V_D=400V Gate Open T_j =125		MIN.	150	V s
(dI/dt)c	(dV/dt)c=10V s, T_j=125		MIN.	1	A/ms
t_{on}	I_G=10mA I_A=200mA I_R=20mA T_j=25		TYP.	2	s
t_{off}				20	

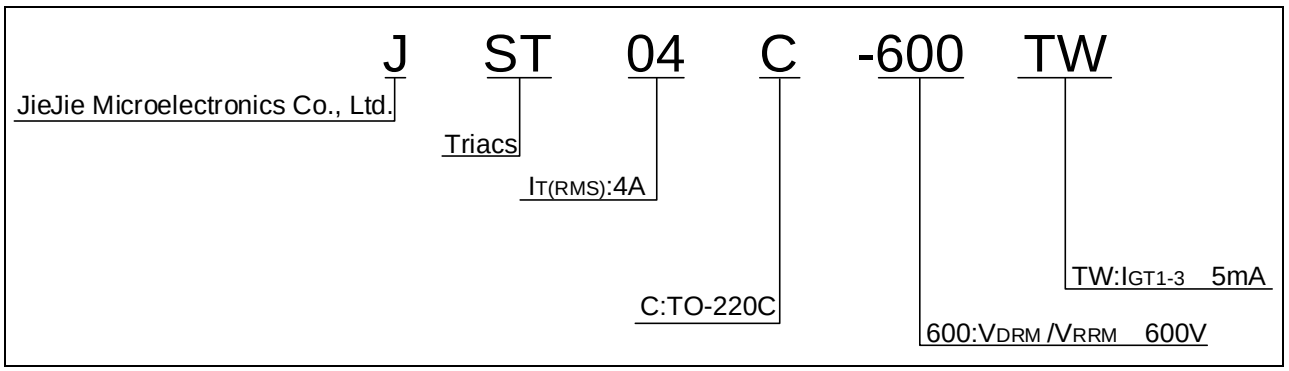
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =5A t_p=380 s	T_j=25	1.65	V
V_{TO}	Threshold voltage	T_j=125	0.799	V
R_D	Dynamic resistance	T_j=125	151	m
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.2	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

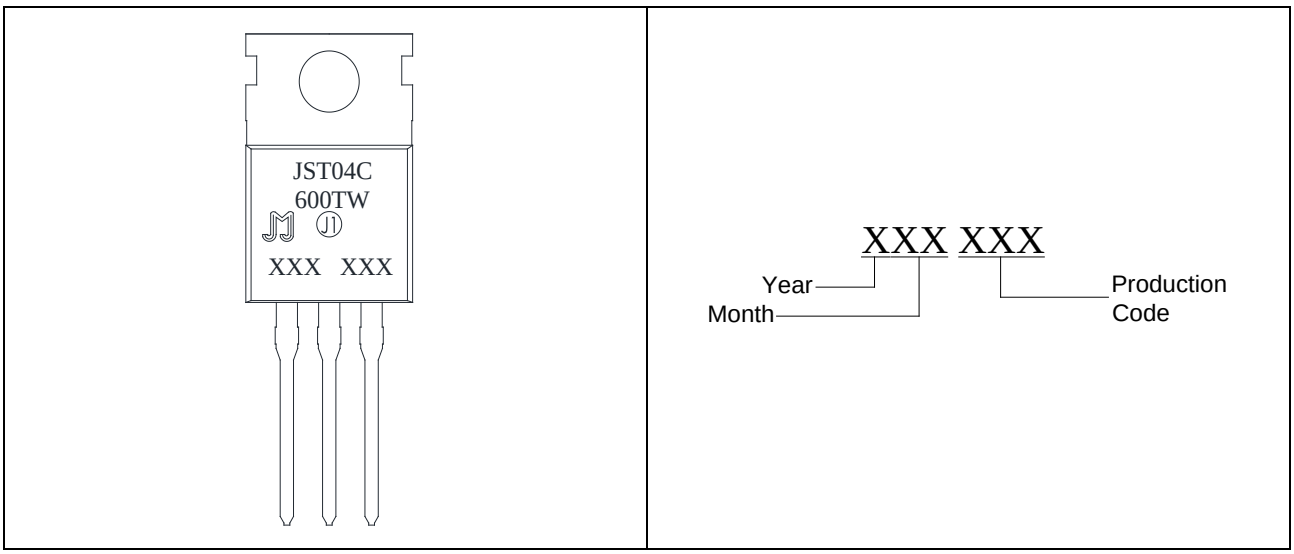


FIG.1: Maximum power dissipation versus RMS on-state current

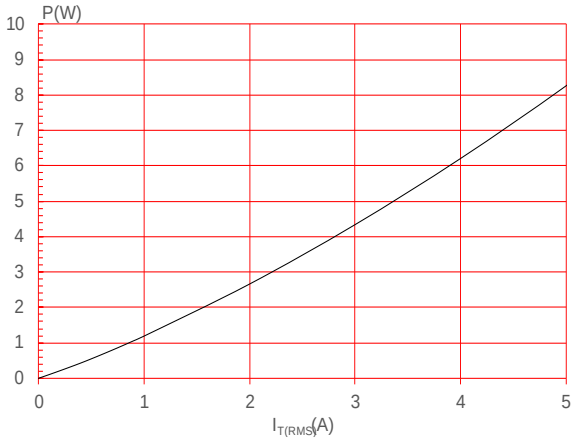
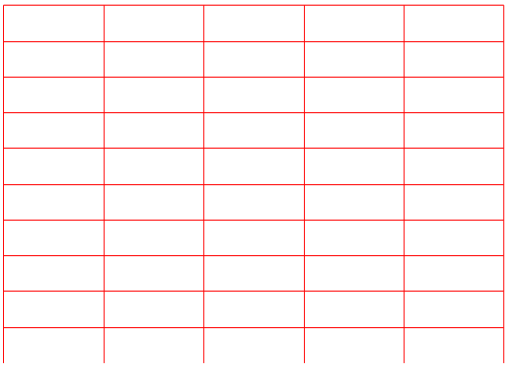


FIG.2: RMS on-state current versus case temperature

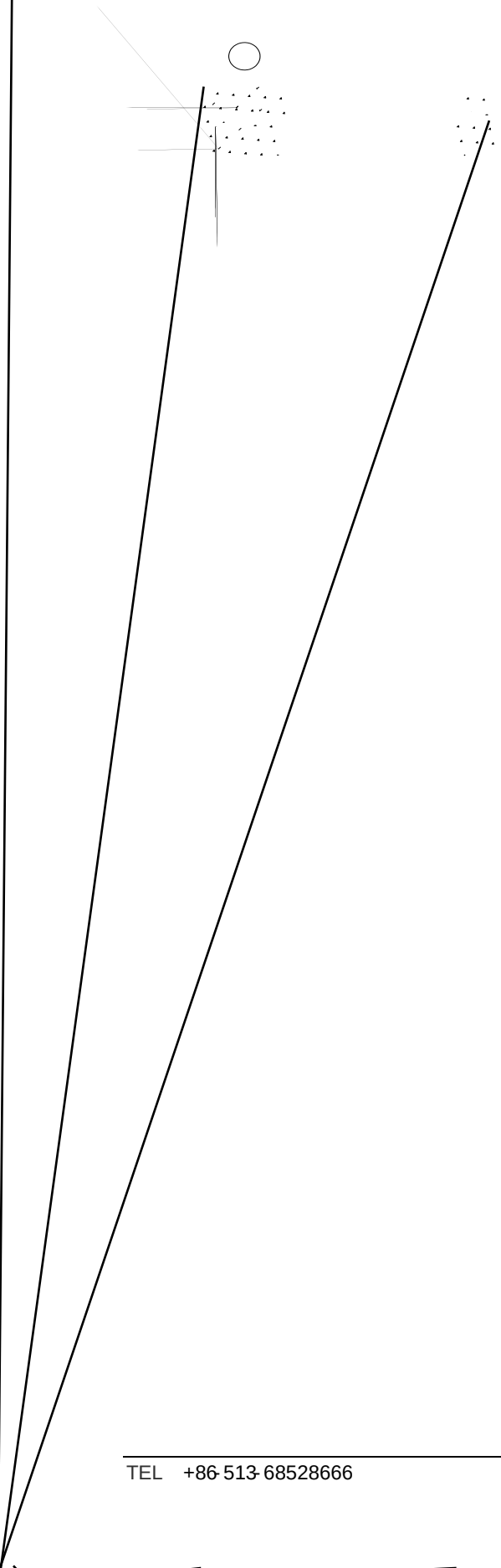


ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST04C-600TW	600	5	TO-220C	50	Tube

Document Revision History

PACKAGE MECHANICAL DATA



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